优尚

YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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Product Summary

BV_{DSS}	Max $R_{DS(ON)}$	Max I_D @ T_A = 25°C
-30V	1Ω @ V_{GS} = -4.5V	-0.67A
	1.5Ω @ V_{GS} = -2.5V	-0.54A
	2Ω @ V_{GS} = -1.8V	-0.47A

Features and Benefits

- Low Gate Threshold Voltage
- Fast Switching Speed

Description and Applications

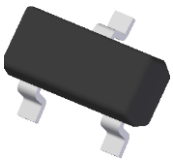
This MOSFET is designed to minimize the on-state resistance ($R_{DS(ON)}$), yet maintain superior switching performance, making it ideal for high efficiency power management applications.

- Load Switch in Portable Electronics

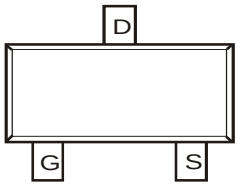
Mechanical Data

- Case: SOT23
- Case Material: Molded Plastic, “Green” Molding Compound. UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Annealed over Copper Leadframe. Solderable per MIL-STD-202, Method 208 e3
- Terminals Connections: See Diagram Below
- Weight: 0.009 grams (Approximate)

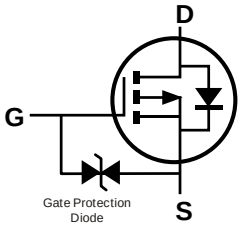
SOT23



Top View



Top View
Internal Schematic



Equivalent Circuit

Maximum Ratings (@T_A = +25°C, unless otherwise specified.)

Characteristic			Symbol	Value	Unit
Drain-Source Voltage			V_{DSS}	-30	V
Gate-Source Voltage			V_{GSS}	±8	V
Continuous Drain Current	Steady State	T_A = +25°C (Note 6) T_A = +85°C (Note 6) T_A = +25°C (Note 5)	I_D	-0.67 -0.48 -0.53	A
Pulsed Drain Current (Note 7)			I_{DM}	2.5	A

Thermal Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic		Symbol	Value	Unit
Power Dissipation	(Note 5)	P_D	0.45	W
	(Note 6)		0.71	W
Thermal Resistance, Junction to Ambient	(Note 5)	$R_{\theta JA}$	275	°C/W
	(Note 6)		177	°C/W
Operating and Storage Temperature Range		T_J, T_{STG}	-55 to +150	°C

Notes: 5. Device mounted on FR-4 PCB, with minimum recommended pad layout
6. Device mounted on 1" x 1" FR-4 PCB with high coverage 2oz. Copper, single sided.
7. Device mounted on minimum recommended pad layout test board, 10µs pulse duty cycle = 1%.

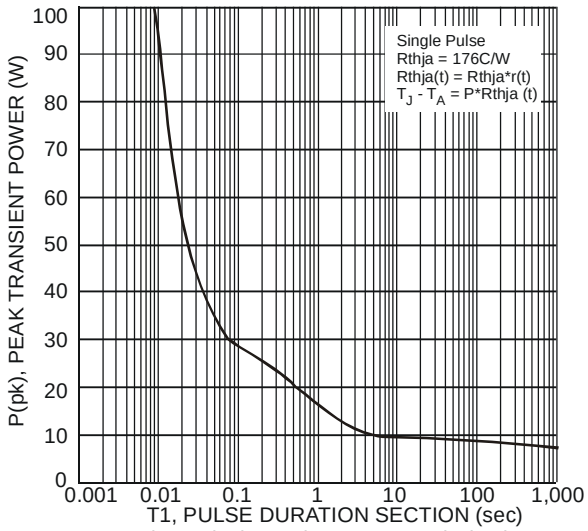


Fig. 1 Single Maximum Power Dissipation

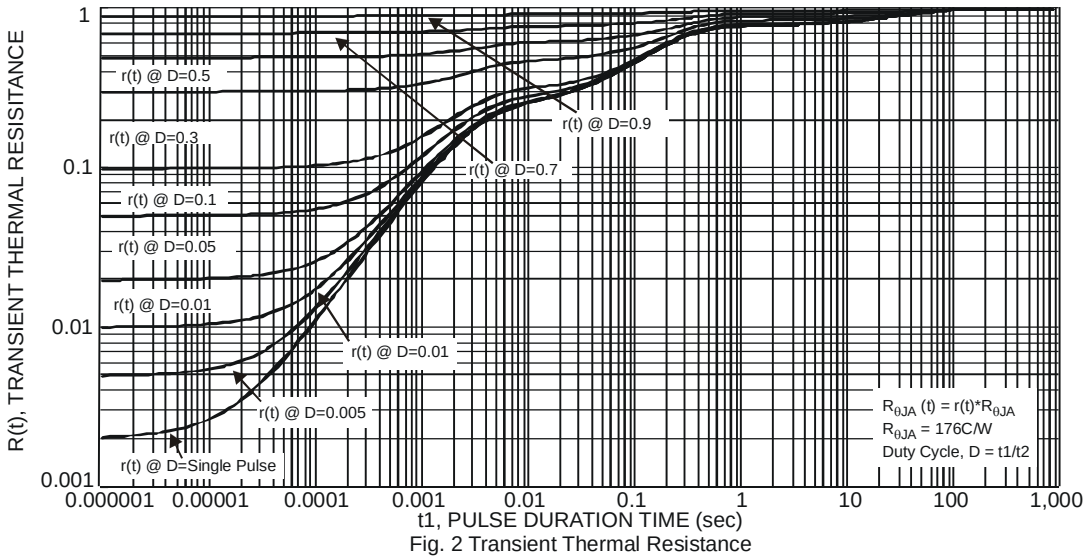


Fig. 2 Transient Thermal Resistance

Electrical Characteristics (@T_A = +25°C, unless otherwise specified.)

Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
OFF CHARACTERISTICS (Note 8)						
Drain-Source Breakdown Voltage	BV_{DSS}	-30	—	—	V	V_{GS} = 0V, I_D = -250μA
Zero Gate Voltage Drain Current T_J = 25°C	I_{DSS}	—	—	-1	μA	V_{DS} = -30V, V_{GS} = 0V
Gate-Source Leakage	I_{GSS}	—	—	±3	μA	V_{GS} = ±8V, V_{DS} = 0V
ON CHARACTERISTICS (Note 8)						
Gate Threshold Voltage	$V_{GS(TH)}$	-0.5	—	-1.1	V	V_{DS} = V_{GS}, I_D = -250μA
Static Drain-Source On-Resistance	$R_{DS\ (ON)}$	—	—	1	Ω	V_{GS} = -4.5V, I_D = -400mA
				1.5		V_{GS} = -2.5V, I_D = -200mA
				2		V_{GS} = -1.8V, I_D = -100mA
Forward Transfer Admittance	$\|Y_{FS}\|$	50	—	—	mS	V_{DS} = -3V, I_D = -300mA
Diode Forward Voltage	V_{SD}	—	—	-1.2	V	V_{GS} = 0V, I_S = -300mA
DYNAMIC CHARACTERISTICS (Note 9)						
Input Capacitance	C_{ISS}	—	76	150	pF	V_{DS} = -15V, V_{GS} = 0V, f = 1.0MHz
Output Capacitance	C_{OSS}	—	9	—	pF	
Reverse Transfer Capacitance	C_{RSS}	—	6.43	—	pF	
Gate Resistance	R_G	—	167	—	Ω	V_{DS} = 0V, V_{GS} = 0V, f = 1MHz
Total Gate Charge	Q_G	—	0.9	—	nC	V_{GS} = -4.5V, V_{DS} = -15V, I_D = -1A
Total Gate Charge	Q_G	—	1.5	—	nC	V_{GS} = -8V, V_{DS} = -15V, I_D = -1A
Gate-Source Charge	Q_{GS}	—	0.1	—	nC	
Gate-Drain Charge	Q_{GD}	—	0.2	—	nC	
Turn-On Delay Time	$t_{D(ON)}$	—	5.0	—	ns	V_{DD} = -10V, R_L = 10Ω, V_{GS} = -4.5V, R_G = 6Ω
Turn-On Rise Time	t_R	—	5.9	—	ns	
Turn-Off Delay Time	$t_{D(OFF)}$	—	35.7	—	ns	
Turn-Off Fall Time	t_F	—	16.7	—	ns	

Notes: 8. Short duration pulse test used to minimize self-heating effect.
9. Guaranteed by design. Not subject to product testing.

Typical Electrical Characteristics

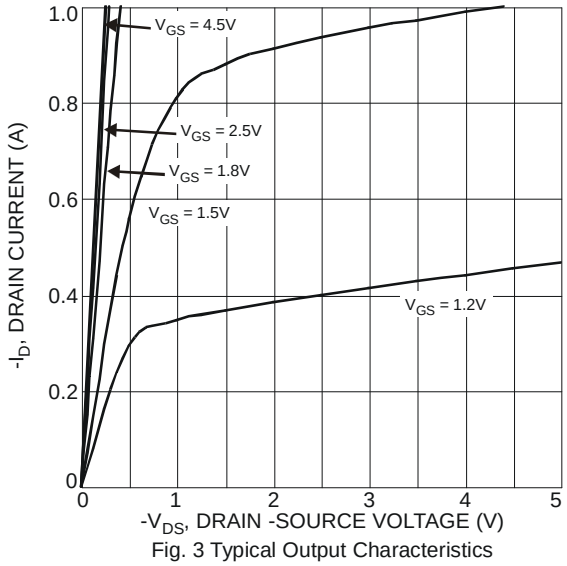


Fig. 3 Typical Output Characteristics

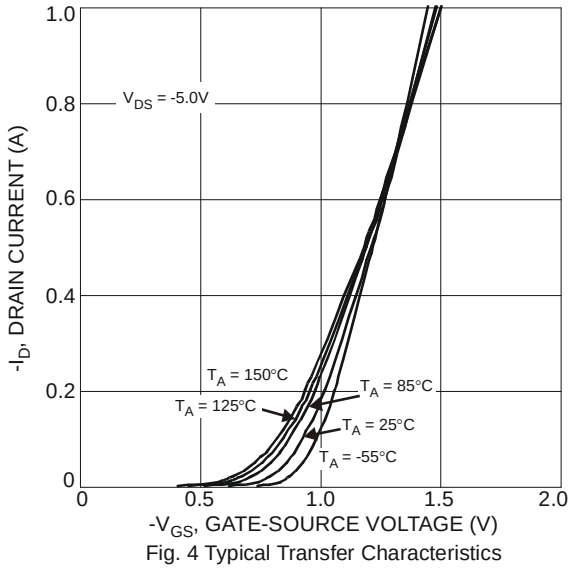


Fig. 4 Typical Transfer Characteristics

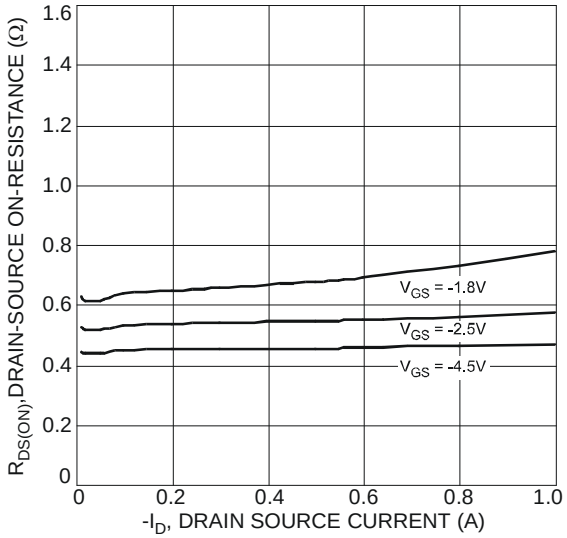


Fig. 5 Typical On-Resistance vs. Drain Current and Gate Voltage

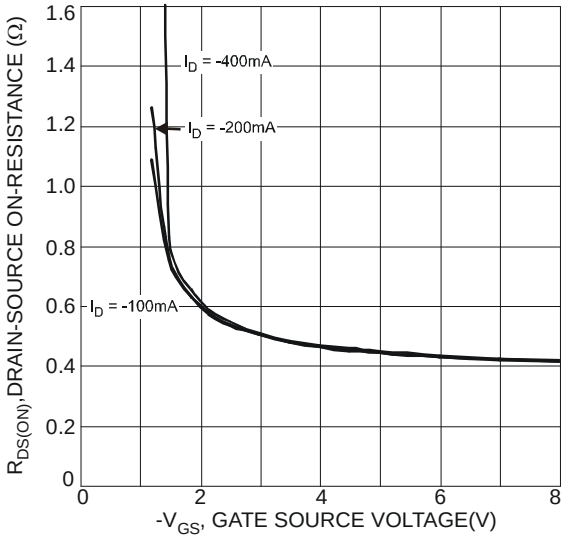


Fig. 6 Typical On-Resistance vs. Drain Current and Gate Voltage

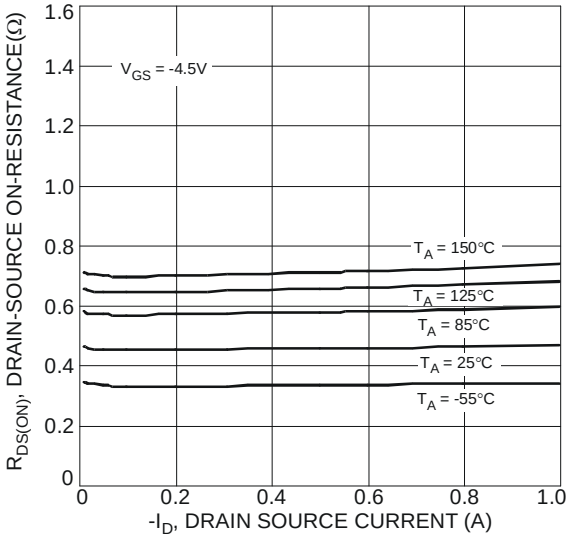


Fig. 7 Typical On-Resistance vs. Drain Current and Temperature

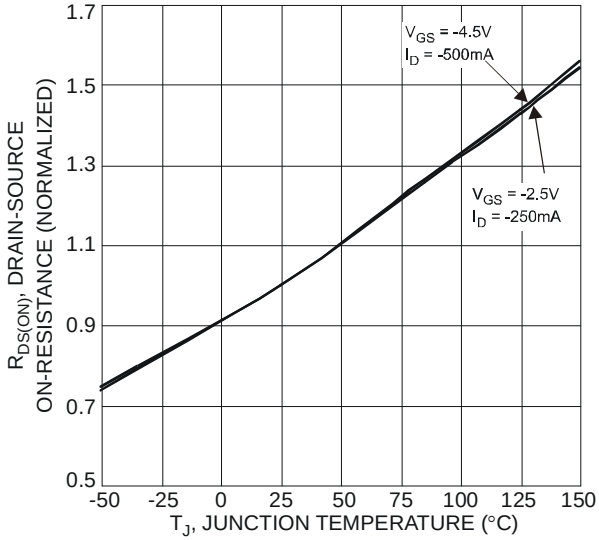


Fig. 8 On-Resistance Variation with Temperature

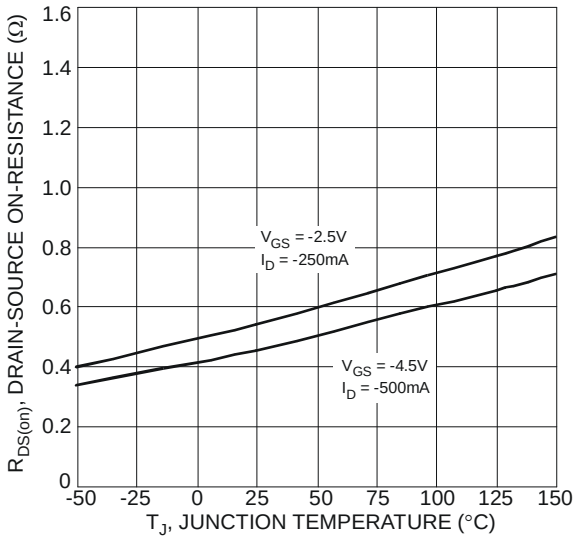


Fig. 9 On-Resistance Variation with Temperature

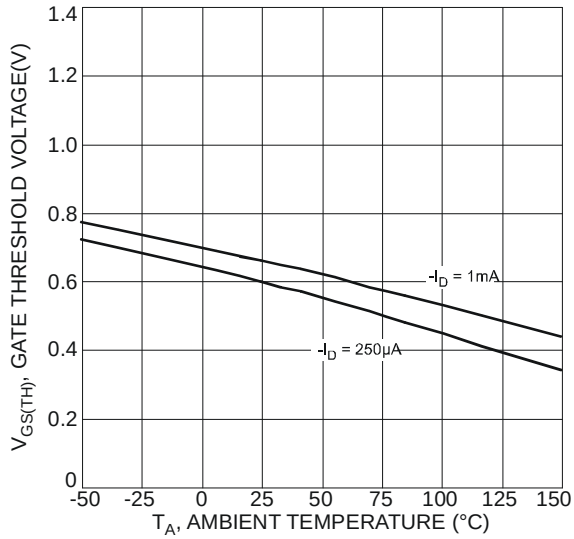


Fig. 10 Gate Threshold Variation vs. Ambient Temperature

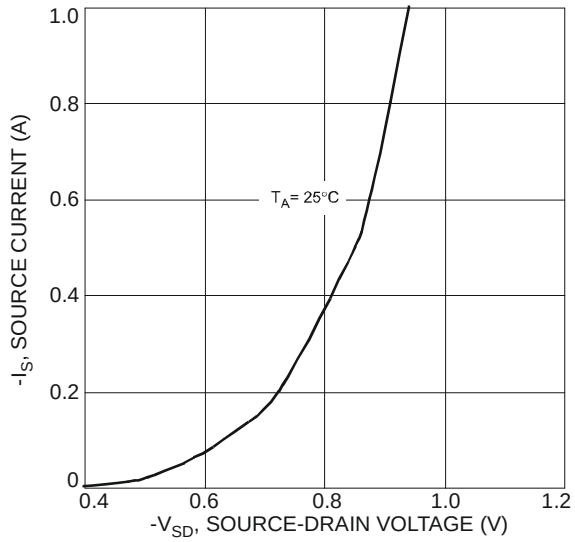


Fig. 11 Diode Forward Voltage vs. Current

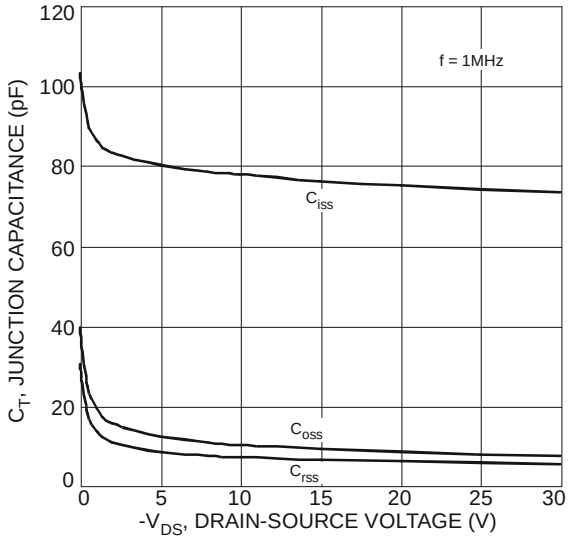


Fig. 12 Typical Junction Capacitance

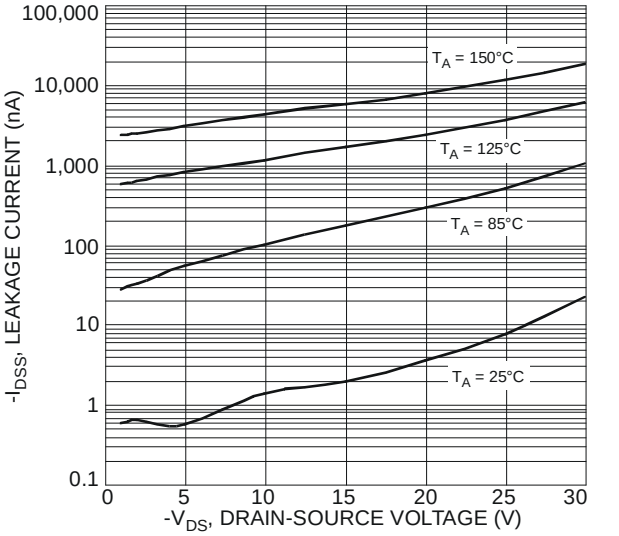


Fig. 13 Typical Drain-Source Leakage Current vs. Voltage

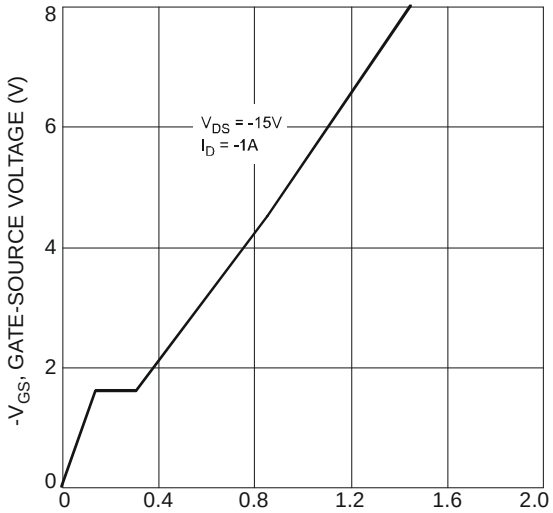
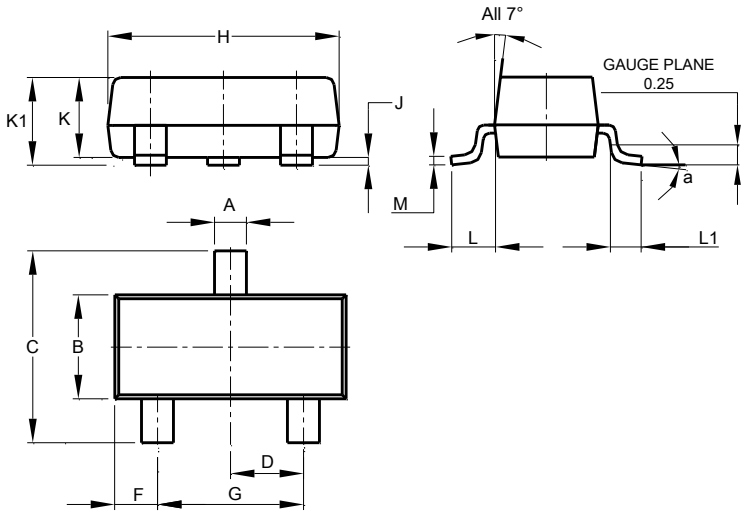


Fig. 14 Gate-Charge Characteristics

Package Outline Dimensions

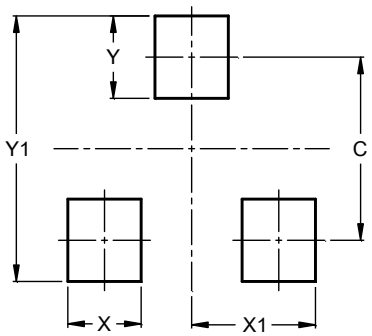
SOT23



SOT23			
Dim	**Min**	**Max**	**Typ**
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.890	1.00	0.975
K1	0.903	1.10	1.025
L	0.45	0.61	0.55
L1	0.25	0.55	0.40
M	0.085	0.150	0.110
a	0°	8°	–
All Dimensions in mm			

Suggested Pad Layout

SOT23



Dimensions	Value (in mm)
C	2.0
X	0.8
X1	1.35
Y	0.9
Y1	2.9